

ABSTRACT OF THE DISCLOSURE

Processes for controlling thickness uniformity of thin organosilicate films as they are deposited on a substrate, and as they finally result. During deposition of the film, which may be accomplished by CVD, PECVD, rapid thermal processing or the like, the substrate temperature is controlled to establish a temperature profile particularly suited to the extreme temperature sensitivities of the deposition rates of organosilicate films such as those deposited from TEOS as a source material.

"SECRET" SECTION